

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of

T. HASHIMOTO et al

Serial No.

Filed: March 4, 2002

For: A SEMICONDUCTOR DEVICE AND A METHOD OF
MANUFACTURING THE SAME

PRELIMINARY AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

Sir:

Prior to the examination thereof, please amend the above-
identified application as follows.

IN THE CLAIMS

Please rewrite claim 14 as set forth below.

14. (Amended) The semiconductor device according to
claim 11, wherein the epitaxial layer is comprised mainly of
silicon-germanium, silicon-germanium-carbon, or silicon.

REMARKS

Claim 14 has been amended to remove its multiple dependency. Examination is respectfully requested.

Respectfully submitted,

John R. Mattingly
Registration No. 30,293
Attorney for Applicants

MATTINGLY, STANGER & MALUR
1800 Diagonal Rd., Suite 370
Alexandria, Virginia 22314
(703) 684-1120
Date: March 4, 2002

卷之三

MARKED UP VERSION OF REWRITTEN CLAIMS

14. (Amended) The semiconductor device according to
claim 11 [or claim 12], wherein the epitaxial layer is
comprised mainly of silicon-germanium, silicon-germanium-
carbon, or silicon.

204050, 68988001